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Kind regards,

Team Nexperia

74HC165; 74HCT165

8-bit parallel-in/serial out shift register Rev. 4 — 28 December 2015

Product data sheet

1. **General description**

The 74HC165; 74HCT165 is an 8-bit serial or parallel-in/serial-out shift register. The device features a serial data input (DS), eight parallel data inputs (D0 to D7) and two complementary serial outputs (Q7 and Q7). When the parallel load input (PL) is LOW the data from D0 to D7 is loaded into the shift register asynchronously. When PL is HIGH data enters the register serially at DS. When the clock enable input (CE) is LOW data is shifted on the LOW-to-HIGH transitions of the CP input. A HIGH on CE will disable the CP input. Inputs include clamp diodes, this enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Asynchronous 8-bit parallel load
- Synchronous serial input
- Complies with JEDEC standard no. 7A
- Input levels:
 - ◆ For 74HC165: CMOS level ◆ For 74HCT165: TTL level
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

Applications 3.

Parallel-to-serial data conversion

Ordering information

Ordering information Table 1.

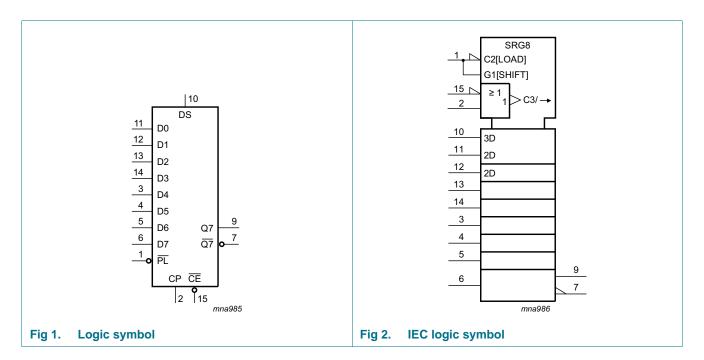
Type number	Package			
	Temperature range	Name	Description	Version
74HC165D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT165D				
74HC165DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1
74HCT165DB			body width 5.3 mm	

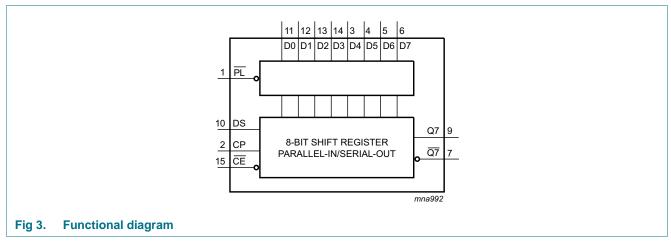


 Table 1.
 Ordering information ...continued

Type number	Package			
	Temperature range	Name	Description	Version
74HC165PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body	SOT403-1
74HCT165PW			width 4.4 mm	
74HC165BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin	SOT763-1
74HCT165BQ			quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	

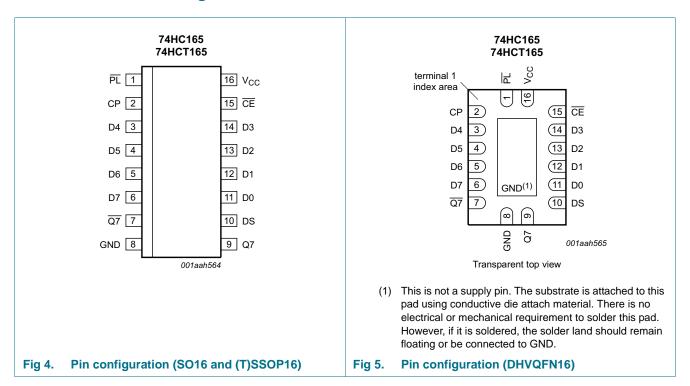
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
PL	1	asynchronous parallel load input (active LOW)
CP	2	clock input (LOW-to-HIGH edge-triggered)
Q7	7	complementary output from the last stage
GND	8	ground (0 V)
Q7	9	serial output from the last stage
DS	10	serial data input
D0 to D7	11, 12, 13, 14, 3, 4, 5, 6	parallel data inputs (also referred to as Dn)
CE	15	clock enable input (active LOW)
V _{CC}	16	positive supply voltage

7. Functional description

Table 3. Function table[1]

Operating modes	Inputs					Qn reg	isters	Outputs		
	PL	CE	СР	DS	D0 to D7	Q0	Q1 to Q6	Q7	Q7	
parallel load	L	Х	Х	Х	L	L	L to L	L	Н	
	L	Х	Х	Х	Н	Н	H to H	Н	L	
serial shift	Н	L	1	I	Х	L	q0 to q5	q6	q 6	
	Н	L	1	h	Х	Н	q0 to q5	q6	q 6	
	Н	1	L	I	Х	L	q0 to q5	q6	q 6	
	Н	1	L	h	Х	Н	q0 to q5	q6	q 6	
hold "do nothing"	Н	Н	Х	Х	Х	q0	q1 to q6	q7	q 7	
	Н	Х	Н	Х	Х	q0	q1 to q6	q7	q 7	

[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;

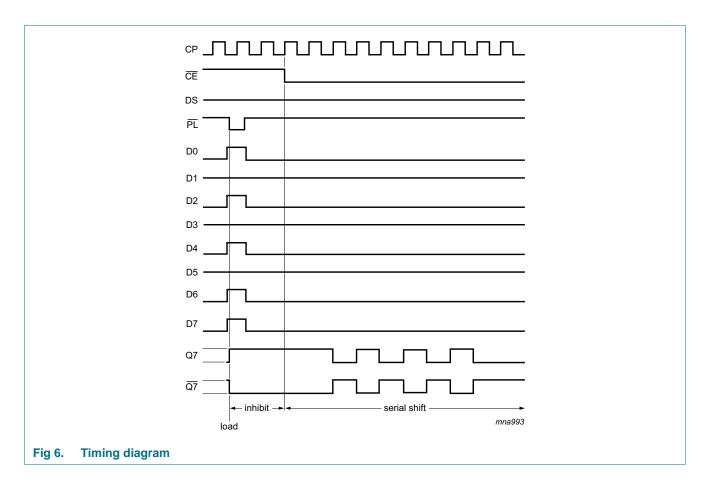
L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;

q = state of the referenced output one set-up time prior to the LOW-to-HIGH clock transition;

X = don't care;

 \uparrow = LOW-to-HIGH clock transition.



74HC_HCT165

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		Min	Max	Unit
V _C C	supply voltage			-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	[1]	-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	[1]	-	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$		-	±25	mA
I _{CC}	supply current			-	50	mA
I _{GND}	ground current			-50	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$				
		SO16 package	[2]	-	500	mW
		(T)SSOP16 package	[3]	-	500	mW
		DHVQFN16 package	<u>[4]</u>	-	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC165			74HCT165			Unit	
			Min	Тур	Max	Min	Тур	Max		
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V	
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V	
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C	
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V	
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V	
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V	

^[2] Ptot derates linearly with 8 mW/K above 70 °C.

^[3] Ptot derates linearly with 5.5 mW/K above 60 °C.

^[4] Ptot derates linearly with 4.5 mW/K above 60 °C.

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC16	5									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	٧
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	٧
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	٧
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	٧
V _{ОН}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_{O} = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_{O} = -20 \mu A; V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	٧
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	٧
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μА
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT1	65							I .		
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	8.0	-	0.8	-	0.8	V
V _{ОН}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μА

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C		-40 °C to	o +85 °C	-40 °C to	Unit		
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V								
		Dn and DS inputs	-	35	126	-	157.5	-	171.5	μΑ
		CP CE, and PL inputs	-	65	234	-	292.5	-	318.5	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC165	5					1	1			
t _{pd}	propagation delay	CP or $\overline{\text{CE}}$ to Q7, $\overline{\text{Q7}}$; see Figure 7								
		V _{CC} = 2.0 V	-	52	165	-	205	-	250	ns
		V _{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		V _{CC} = 6.0 V	-	15	28	-	35	-	43	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	16	-	-	-	-	-	ns
		PL to Q7, Q7; see Figure 8								
		V _{CC} = 2.0 V	-	50	165	-	205	-	250	ns
		V _{CC} = 4.5 V	-	18	33	-	41	-	50	ns
		V _{CC} = 6.0 V	-	14	28	-	35	-	43	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	15	-	-	-	-	-	ns
		D7 to Q7, Q7; see Figure 9								
		V _{CC} = 2.0 V	-	36	120	-	150	-	180	ns
		V _{CC} = 4.5 V	-	13	24	-	30	-	36	ns
		V _{CC} = 6.0 V	-	10	20	-	26	-	31	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	-	-	-	-	ns
t _t	transition	Q7, Q7 output; see Figure 7 2								
	time	V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

 Table 7.
 Dynamic characteristics ...continued

GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions		25 °C		-40 °C t	-40 °C to +85 °C -40 °C to +125 °C			Unit
			Min	Тур	Max	Min	Max	Min	Max	
t _W	pulse width	CP input HIGH or LOW; see Figure 7								
		V _{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		PL input LOW; see Figure 8								
		V _{CC} = 2.0 V	80	14	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	4	-	17	-	20	-	ns
t _{rec}	recovery time	PL to CP, CE; see Figure 8								
		V _{CC} = 2.0 V	100	22	-	125	-	150	-	ns
		V _{CC} = 4.5 V	20	8	-	25	-	30	-	ns
		V _{CC} = 6.0 V	17	6	-	21	-	26	-	ns
t _{su}	set-up time	DS to CP, CE; see Figure 10								
		V _{CC} = 2.0 V	80	11	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	4	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	3	-	17	-	20	-	ns
		CE to CP and CP to CE; see Figure 10								
		V _{CC} = 2.0 V	80	17	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	5	-	17	-	20	-	ns
		Dn to PL; see Figure 11								
		V _{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	6	-	17	-	20	-	ns
t _h	hold time	DS to CP, $\overline{\text{CE}}$ and Dn to $\overline{\text{PL}}$; see Figure 10								
		V _{CC} = 2.0 V	5	6	-	5	-	5	-	ns
		V _{CC} = 4.5 V	5	2	-	5	-	5	-	ns
		V _{CC} = 6.0 V	5	2	-	5	-	5	-	ns
		CE to CP and CP to CE; see Figure 10								
		V _{CC} = 2.0 V	5	-17	-	5	-	5	-	ns
		V _{CC} = 4.5 V	5	-6	-	5	-	5	-	ns
		V _{CC} = 6.0 V	5	-5	-	5	-	5	-	ns

 Table 7.
 Dynamic characteristics ...continued

GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit, see Figure 12

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
f _{max}	maximum	CP input; see Figure 7								
	frequency	V _{CC} = 2.0 V	6	17	-	5	-	4	-	MHz
		V _{CC} = 4.5 V	30	51	-	24	-	20	-	MHz
		V _{CC} = 6.0 V	35	61	-	28	-	24	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	56	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC}	-	35	-	-	-	-	-	pF
74HCT10	65									
t _{pd}	propagation delay	CE, CP to Q7, Q7; see Figure 7								
		V _{CC} = 4.5 V	-	17	34	-	43	-	51	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	14	-	-	-	-	-	ns
		PL to Q7, Q7; see Figure 8								
		V _{CC} = 4.5 V	-	20	40	-	50	-	60	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	17	-	-	-	-	-	ns
		D7 to Q7, Q7; see Figure 9								
		V _{CC} = 4.5 V	-	14	28	-	35	-	42	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	11	-	-	-	-	-	ns
t _t	transition	Q7, Q7 output; see Figure 7								
	time	V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t _W	pulse width	CP input; see Figure 7								
		V _{CC} = 4.5 V	16	6	-	20	-	24	-	ns
		PL input; see Figure 8								
		V _{CC} = 4.5 V	20	9	-	25	-	30	-	ns
t _{rec}	recovery time	PL to CP, CE; see Figure 8								
		V _{CC} = 4.5 V	20	8	-	25	-	30	-	ns
t _{su}	set-up time	DS to CP, CE; see Figure 10								
		V _{CC} = 4.5 V	20	2	-	25	-	30	-	ns
		CE to CP and CP to CE; see Figure 10								
		V _{CC} = 4.5 V	20	7	-	25	-	30	-	ns
		Dn to PL; see Figure 11								
		V _{CC} = 4.5 V	20	10	-	25	-	30	-	ns
t _h	hold time	DS to CP, CE and Dn to PL; see Figure 10								
		V _{CC} = 4.5 V	7	-1	-	9	-	11	-	ns
		CE to CP and CP to CE; see Figure 10								
		V _{CC} = 4.5 V	0	-7	-	0	-	0	-	ns

 Table 7.
 Dynamic characteristics ...continued

GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see <u>Figure 12</u>

Symbol	Parameter	Conditions	25 °C -		–40 °C to	+85 °C	–40 °C to	Unit		
			Min	Тур	Max	Min	Max	Min	Max	
f _{max}	maximum	CP input; see Figure 7								
	frequency	V _{CC} = 4.5 V	26	44	-	21	-	17	-	MHz
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$	-	48	-	-	-	-	-	MHz
C _{PD}	power dissipation capacitance	per package; [3] $V_I = GND \text{ to } V_{CC} - 1.5 \text{ V}$	-	35	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

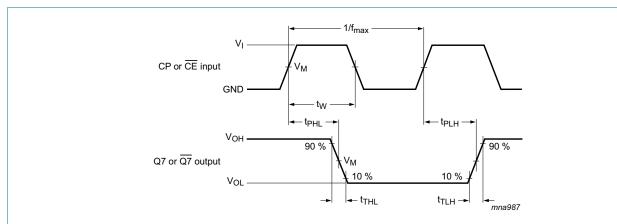
f_o = output frequency in MHz;

 $\Sigma (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs};$

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V.

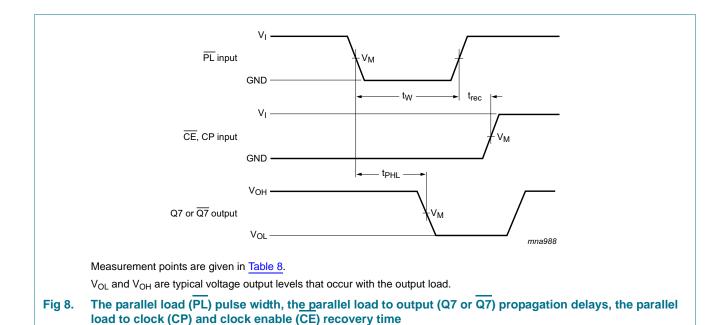
12. Waveforms

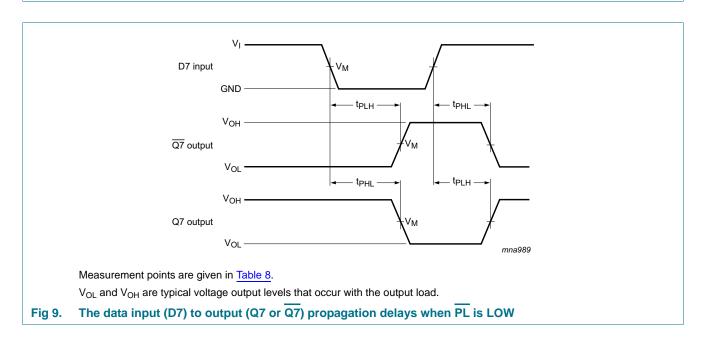


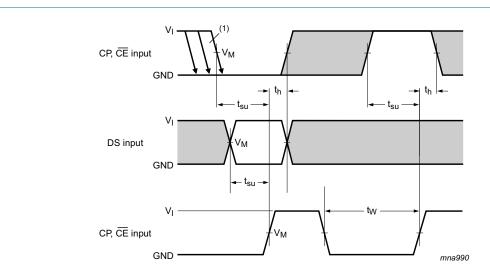
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. The clock (CP) or clock enable (CE) to output (Q7 or Q7) propagation delays, the clock pulse width, the maximum clock frequency and the output transition times





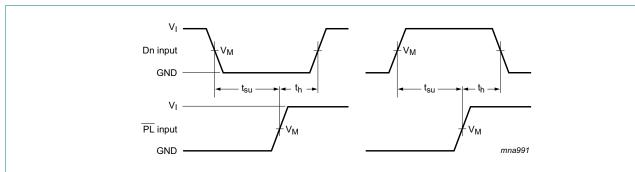


The shaded areas indicate when the input is permitted to change for predictable output performance Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

(1) $\overline{\text{CE}}$ may change only from HIGH-to-LOW while CP is LOW, see Section 1.

Fig 10. The set-up and hold times from the serial data input (DS) to the clock (CP) and clock enable (CE) inputs, from the clock enable input (CE) to the clock input (CP) and from the clock input (CP) to the clock enable input (CE)



Measurement points are given in Table 8.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

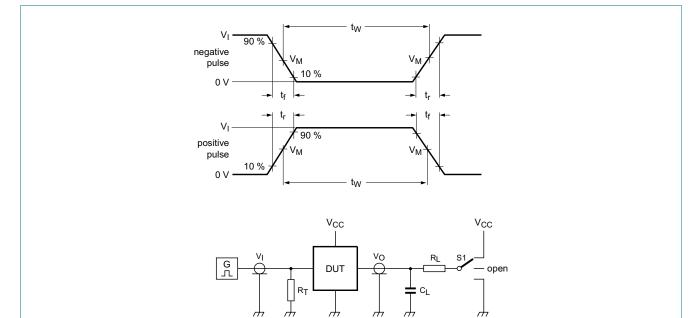
Fig 11. The set-up and hold times from the data inputs (Dn) to the parallel load input (PL)

Table 8. Measurement points

Туре	Input		Output
	VI	V _M	V _M
74HC165	V _{CC}	0.5V _{CC}	0.5V _{CC}
74HCT165	3 V	1.3 V	1.3 V

001aad983

8-bit parallel-in/serial out shift register



Test data is given in Table 9.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch

Fig 12. Test circuit for measuring switching times

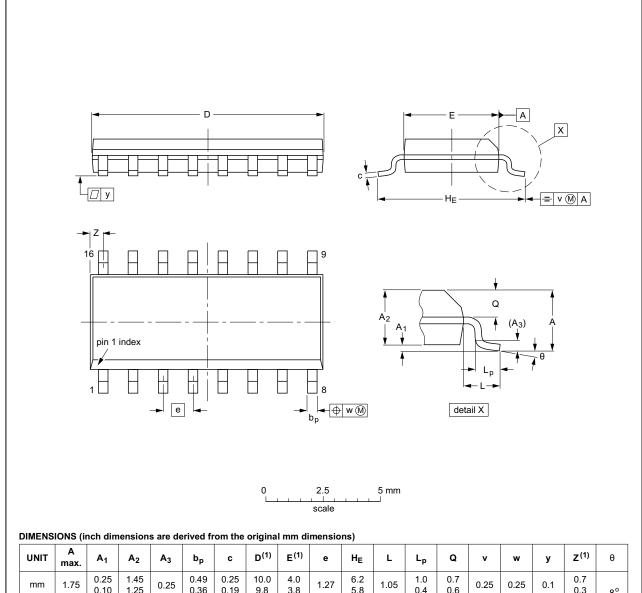
Table 9. Test data

Туре	Input		Load	S1 position	
	VI	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}
74HC165	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT165	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

	REFER	RENCES	EUROPEAN	ISSUE DATE
IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
076E07	MS-012			99-12-27 03-02-19
	-	IEC JEDEC	IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 13. Package outline SOT109-1 (SO16)

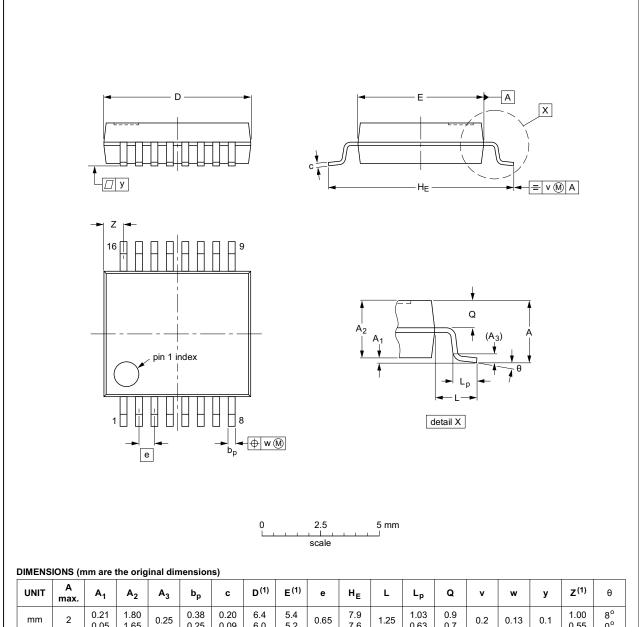
74HC_HCT165

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	C	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

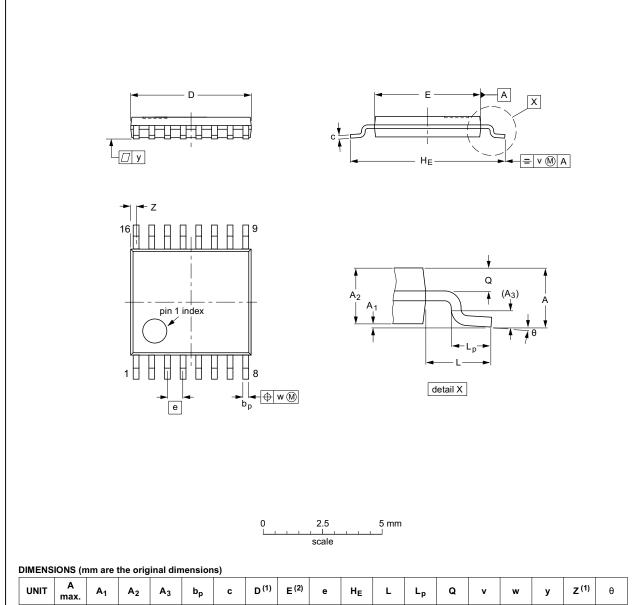
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT338-1		MO-150				99-12-27 03-02-19

Fig 14. Package outline SOT338-1 (SSOP16)

74HC_HCT165

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

(OUTLINE		REFER	EUROPEAN	ISSUE DATE		
\	/ERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	SOT403-1		MO-153				99-12-27 03-02-18

Fig 15. Package outline SOT403-1 (TSSOP16)

74HC_HCT165

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

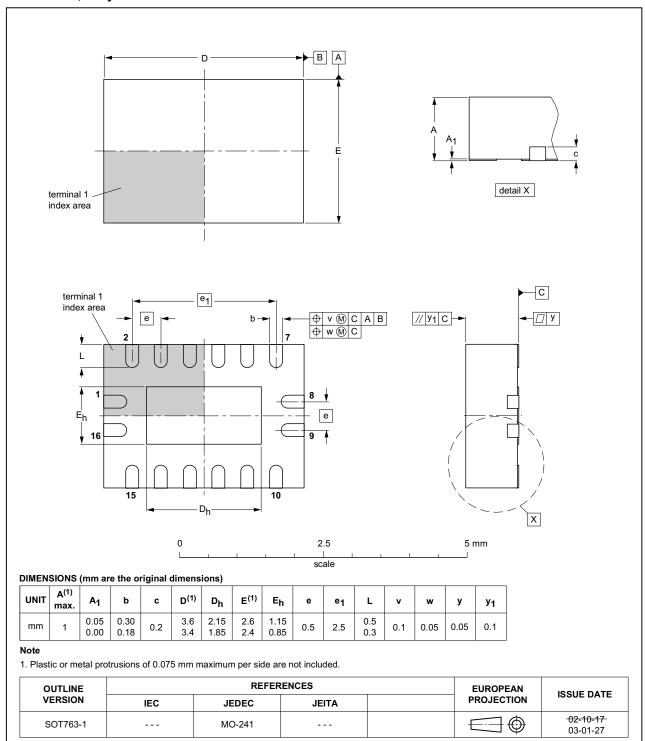


Fig 16. Package outline SOT763-1 (DHVQFN16)

74HC_HCT165

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT165 v.4	20151228	Product data sheet	-	74HC_HCT165 v.3
Modifications:	Type numbers	s 74HC165N and 74HCT165N	(SOT38-4) removed	d.
74HC_HCT165 v.3	20080314	Product data sheet	-	74HC_HCT165_CNV v.2
Modifications:	guidelines of	this data sheet has been rede NXP Semiconductors. ave been adapted to the new c		•
	13 "Package			information" and Section
	 Family data a 	dded, see <u>Section 10 "Static cl</u>	haracteristics"	
74HC_HCT165_CNV v.2	December 1990	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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74HC165; 74HCT165

8-bit parallel-in/serial out shift register

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